## PROPERTIES OF OXYGEN PRECIPITATES IN NEUTRON IRRADIATED Cz SILICON

V. I. Varnina, A. A. Groza, P. G. Litovchenko, M. I. Starchik, L. A. Polivtsev, G. G. Shmatko, L. S. Marchenko

It was received the acceleration of defect formation and oxygen precipitation in neutron irradiated and annealed (700 °C) Cz silicon. The possibility of oxygen precipitation temperature decrease was shown for irradiated silicon, that was useful for getter metal impurities by oxide precipitates.